AMENDMENTS TO THE CLAIMS:

Please cancel claims 1-10, without prejudice. Kindly amend claims 12 and 13, as shown below.

This listing of claims will replace all prior versions and listings of claims in the Application:

Claims 1 - 10 (cancelled)

Claim 11 (original): A manufacturing method for alignment marks comprising the steps of :

forming a thin-film transistor including at least a gate electrode, a gate insulating film, a semiconductor thin film, source and drain electrodes on a wafer;

forming alignment reference marks by using the same materials as those of at least one of the gate electrode, the semiconductor film, and the source and drain electrodes in an area other than a formation area for the thin-film transistor at the same time when the gate electrode, the semiconductor film and the source and drain electrodes are formed:

forming red filter alignment reference marks comprising a red filter so as to cover the alignment reference marks; and

then, performing alignment of the following step pattern based on the alignment reference marks below the red filter alignment marks.

Claim 12 (currently amended): The manufacturing method for alignment marks as set forth in Claim 11, wherein:

the alignment reference marks are formed at the same time as source and drain electrodes with a shading property are formed, and alignment is performed by means of light reflection caused by the alignment reference marks.

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Claim 13 (currently amended): A manufacturing method for alignment marks comprises the steps of:

forming a thin-film transistor including at least a gate electrode, a gate insulating film, a semiconductor ~~thin film~~ thin-film, source and drain electrodes on a wafer;

forming alignment reference marks by using the same materials as those of at least one of the gate electrode, the semiconductor film, and the source and drain electrodes in an area other than a formation area for the thin-film transistor, at the same time as the gate electrode, the semiconductor film, and the source and drain electrodes are formed;

forming a red filter alignment reference marks comprising a red filter in the area other than the thin-film transistor formation area and distant from the alignment reference marks with the alignment reference marks as a reference; and

then, performing alignment of the following step pattern with the red filter alignment reference marks as a reference.

Claim 14 (original): The manufacturing method for alignment marks as set forth in Claim 13, wherein alignment is performed by diffracted light at a step portion formed by the red filter alignment reference marks.

Claim 15 (original): A manufacturing method for alignment marks comprised the steps of:

forming a thin-film transistor including at least a gate electrode, a gate insulating film, a semiconductor thin film, source and drain electrodes on a wafer;

forming alignment reference marks having a laminated structure comprising the semiconductor thin film and the source and drain electrodes by using the same materials as those of the semiconductor film and the source and drain electrodes composing the thin-film transistor; and then,

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performing alignment of the following step pattern with the laminated structure alignment reference marks as a reference.

Claim 16 (original): The manufacturing method for alignment marks as set forth in Claim 15, wherein the semiconductor film comprises an active semiconductor film as its lower layer and an ohmic semiconductor film as its upper layer.

Claim 17 (original): The manufacturing method for alignment marks as set forth in Claim 15, wherein alignment is performed by diffracted light at a step portion formed by the laminated structure alignment reference marks.

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AMENDMENTS TO THE DRAWINGS:

The attached sheets of drawings include changes to FIGs. 1A and 19A. These sheets, which include FIGS. 1A, 1B, 19A and 19B, replace the original sheets including FIGS. 1A, 1B, 19A and 19B. A marked copy of amended FIGs. 1A and 19A is also enclosed.

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